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MOSFET – Power, Single N-Channel, DFNW8

150 V, 4.45 mΩ, 165 A



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NVMTS4D3N15MC

Features

- Small Footprint (8x8 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

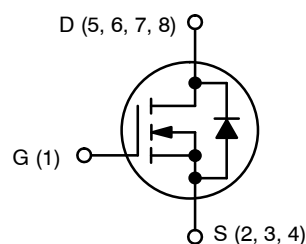
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Value	Unit	
V_{DSS}	Drain-to-Source Voltage		150	V	
V_{GS}	Gate-to-Source Voltage		± 20	V	
I_D	Continuous Drain Current $R_{\theta JC}$ (Note 2)	Steady State	$T_C = 25^\circ\text{C}$	165	A
P_D				Power Dissipation $R_{\theta JC}$ (Note 2)	292
I_D	Continuous Drain Current $R_{\theta JC}$ (Note 2)	Steady State	$T_C = 100^\circ\text{C}$	117	A
P_D				Power Dissipation $R_{\theta JC}$ (Note 2)	146
I_D	Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^\circ\text{C}$	21	A
P_D				Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	5
I_D	Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 100^\circ\text{C}$	15	A
P_D				Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	2.4
I_{DM}	Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	900	A	
T_J, T_{stg}	Operating Junction and Storage Temperature Range		-55 to +175	$^\circ\text{C}$	
I_S	Source Current (Body Diode)		243	A	
E_{AS}	Single Pulse Drain-to-Source Avalanche Energy ($I_L = 14.1 \text{ A}$)		3390	mJ	
T_L	Lead Temperature Soldering Reflow for Soldering Purposes (1/8" from case for 10 s)		260	$^\circ\text{C}$	

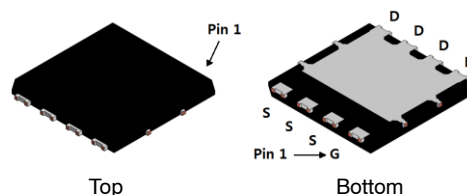
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using 1 in² pad size, 1 oz Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted

$V_{(BR)DSS}$	$R_{DS(ON) MAX}$	$I_D MAX$
150 V	4.45 mΩ @ 10 V	165 A

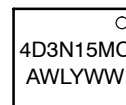


N-CHANNEL MOSFET



DFNW8
CASE 507AP

MARKING DIAGRAM



4D3N15MC = Specific Device Code
A = Assembly Location
WL = Wafer Lot Code
Y = Year Code
WW = Work Week Code

ORDERING INFORMATION

Device	Package	Shipping†
NVMTS4D3N15MC	DFNW8 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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THERMAL RESISTANCE RATINGS

Symbol	Parameter	Max	Unit
$R_{\theta JC}$	Junction-to-Case – Steady State (Note 2)	0.5	°C/W
$R_{\theta JA}$	Junction-to-Ambient – Steady State (Note 2)	31.4	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	150	–	–	V	
$V_{(BR)DSS} / T_J$	Drain-to-Source Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, ref to 25°C	–	49.84	–	mV/°C	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{ V}, V_{DS} = 120\text{ V}$	$T_J = 25^\circ\text{C}$	–	–	1	μA
			$T_J = 125^\circ\text{C}$	–	–	10	μA
I_{GSS}	Gate-to-Source Leakage Current	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	–	–	± 100	nA	

ON CHARACTERISTICS (Note 3)

$V_{GS(TH)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 521\ \mu\text{A}$	2.5	3.6	4.5	V
$V_{GS(TH)} / T_J$	Negative Threshold Temperature Coefficient	$I_D = 250\ \mu\text{A}$, ref to 25°C	–	–9.93	–	mV/°C
$R_{DS(on)}$	Drain-to-Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 95\text{ A}$	–	3.4	4.45	m Ω
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 95\text{ A}$	–	177	–	S
R_G	Gate-Resistance	$T_A = 25^\circ\text{C}$	–	1.1	–	Ω

CHARGES & CAPACITANCES

C_{ISS}	Input Capacitance	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 75\text{ V}$	–	6514	–	pF
C_{OSS}	Output Capacitance		–	1750	–	
C_{RSS}	Reverse Transfer Capacitance		–	12.5	–	
$Q_{G(TOT)}$	Total Gate Charge	$V_{GS} = 10\text{ V}, V_{DS} = 75\text{ V}, I_D = 95\text{ A}$	–	79	–	nC
$Q_{G(TH)}$	Threshold Gate Charge		–	21	–	
Q_{GS}	Gate-to-Source Charge		–	36	–	
Q_{GD}	Gate-to-Drain Charge		–	11	–	
V_{GP}	Plateau Voltage		–	5.8	–	
			–	–	–	

SWITCHING CHARACTERISTICS, $V_{GS} = 10\text{ V}$ (Note 3)

$t_{d(ON)}$	Turn-On Delay Time	$V_{GS} = 10\text{ V}, V_{DS} = 75\text{ V}, I_D = 95\text{ A}, R_G = 6\ \Omega$	–	38	–	ns
t_r	Rise Time		–	11	–	
$t_{d(OFF)}$	Turn-Off Delay Time		–	48	–	
t_f	Fall Time		–	8	–	

DRAIN-SOURCE DIODE CHARACTERISTICS

V_{SD}	Forward Diode Voltage	$V_{GS} = 0\text{ V}, I_S = 95\text{ A}$	$T_J = 25^\circ\text{C}$	–	0.86	1.2	V
			$T_J = 125^\circ\text{C}$	–	0.80	–	
t_{RR}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, di_G/dt = 100\text{ A}/\mu\text{s}, I_S = 95\text{ A}$	–	85	–	ns	
t_a	Charge Time		–	58	–		
t_b	Discharge Time		–	38	–		
Q_{RR}	Reverse Recovery Charge		–	194	–		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures

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TYPICAL CHARACTERISTICS

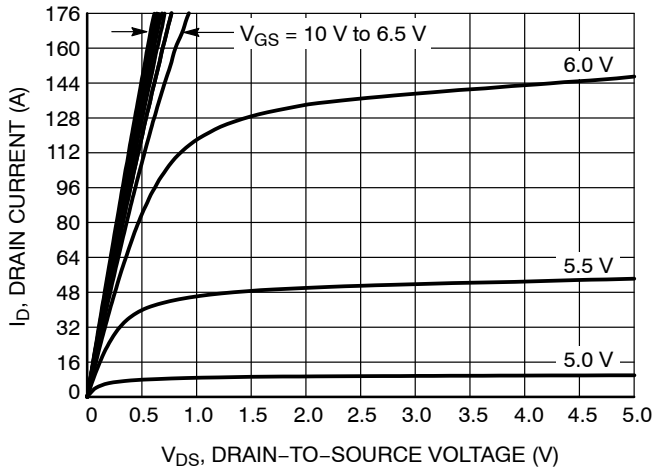


Figure 1. On-Region Characteristics

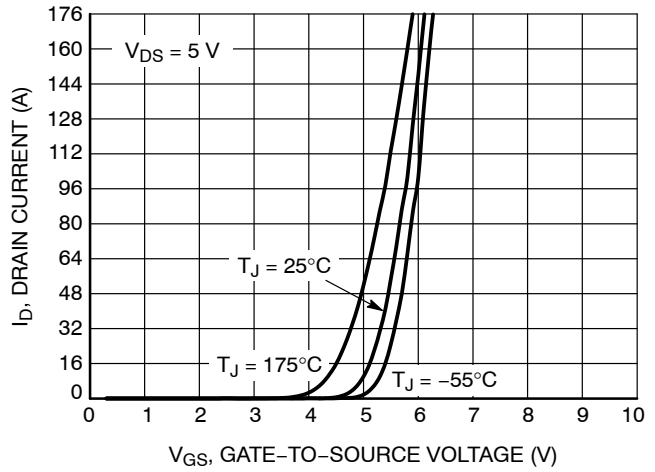


Figure 2. Transfer Characteristics

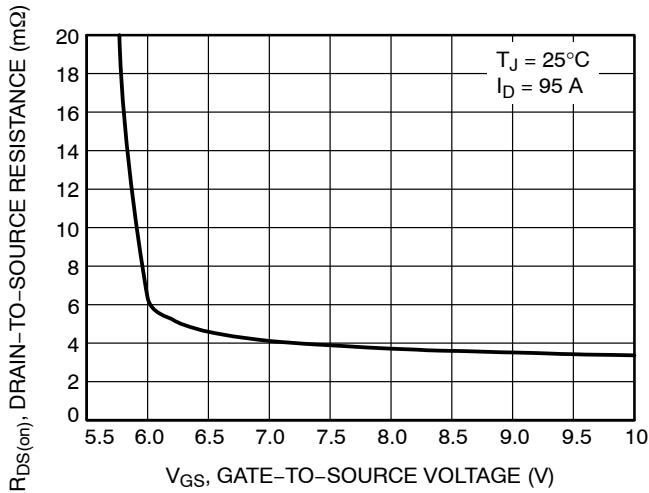


Figure 3. On-Resistance vs. Gate-to-Source Voltage

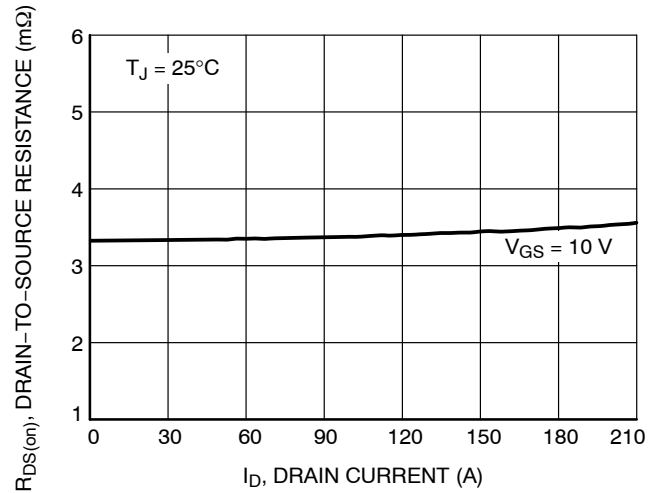


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

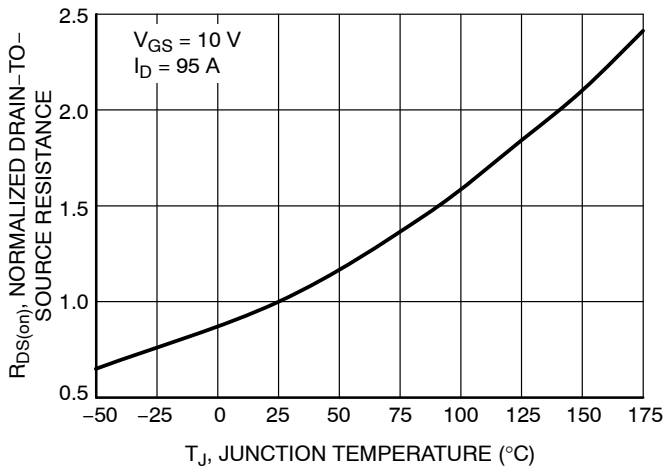


Figure 5. On-Resistance Variation with Temperature

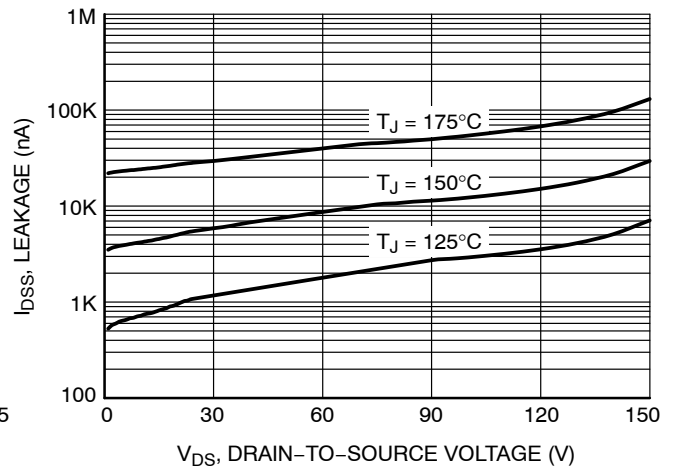


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

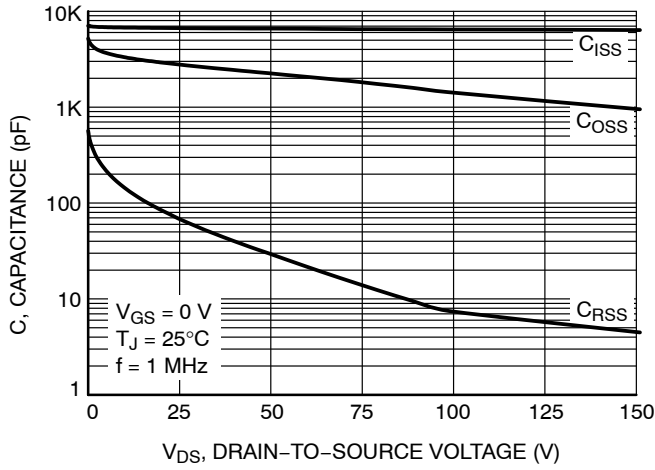


Figure 7. Capacitance Variation

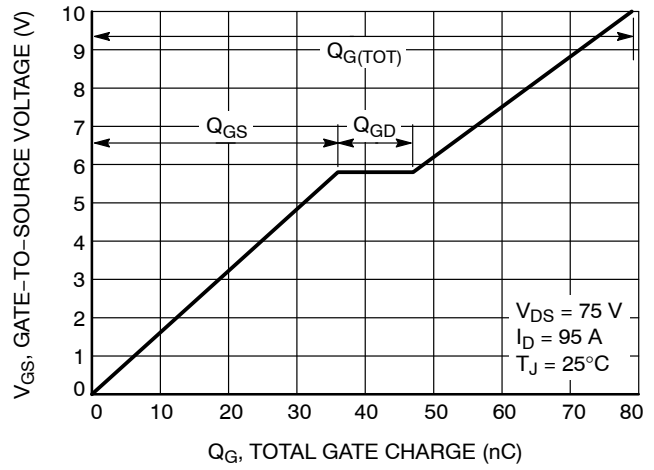


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

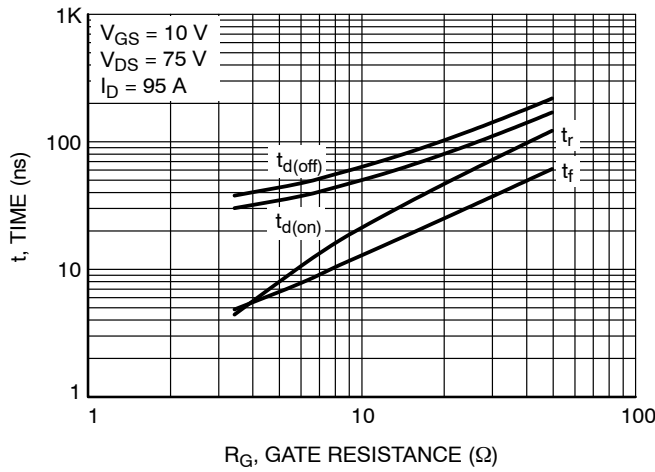


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

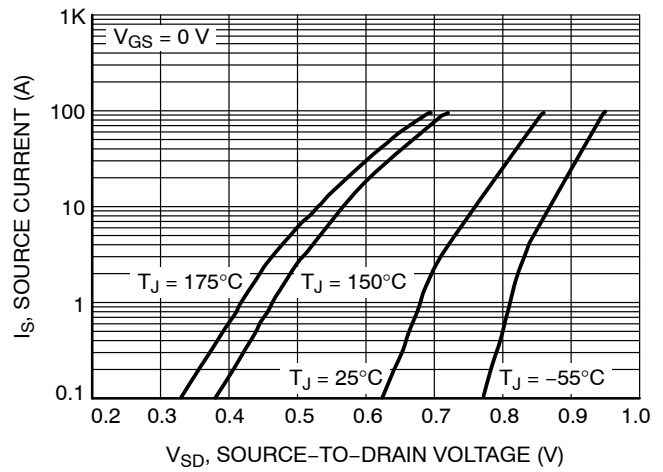


Figure 10. Diode Forward Voltage vs. Current

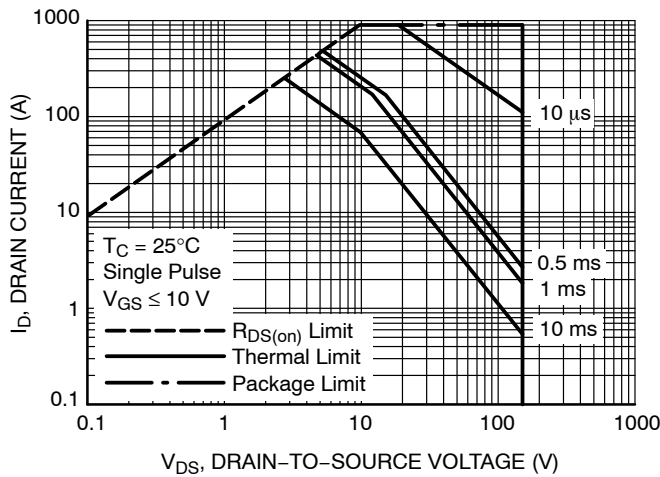


Figure 11. Safe Operating Area

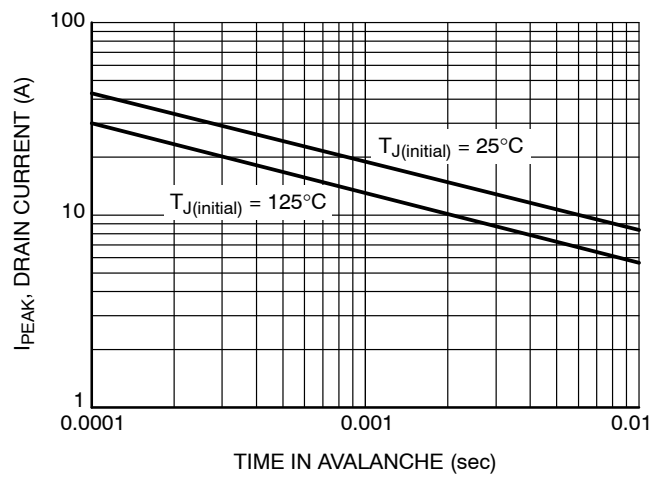


Figure 12. I_{PEAK} vs. Time in Avalanche

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TYPICAL CHARACTERISTICS

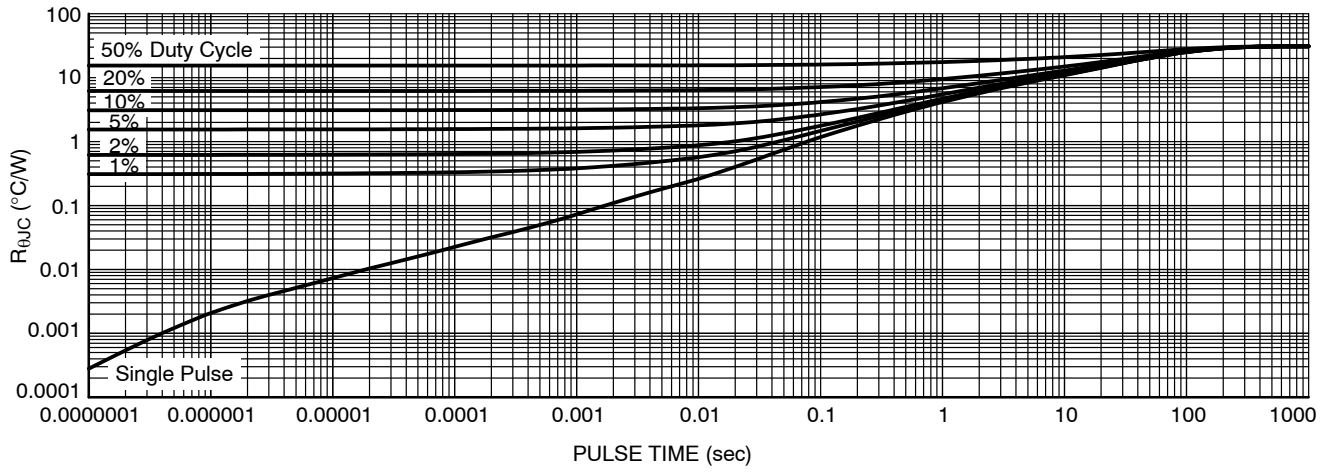
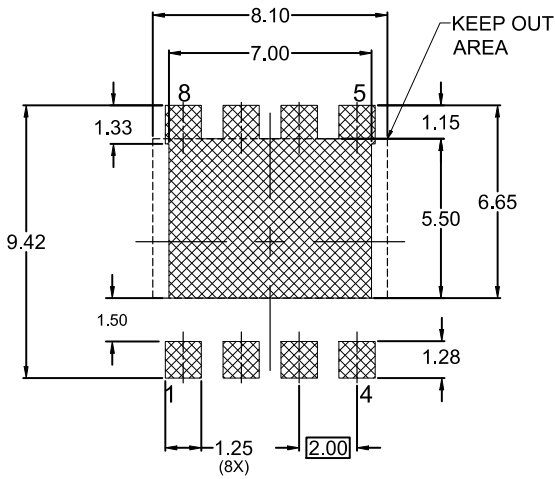
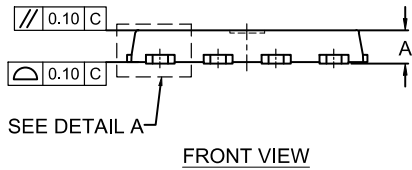
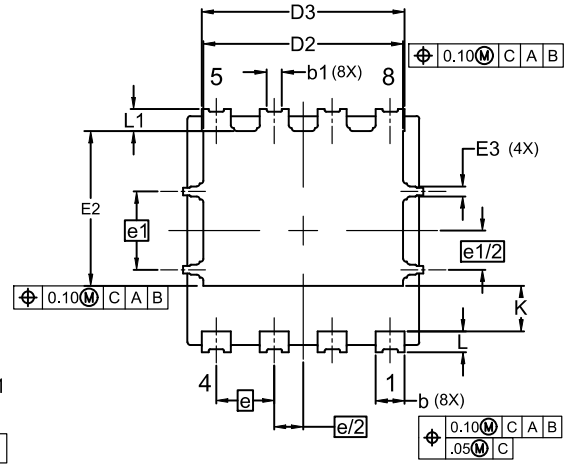
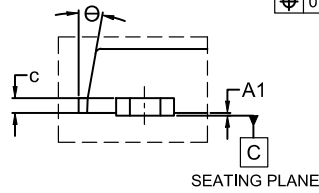
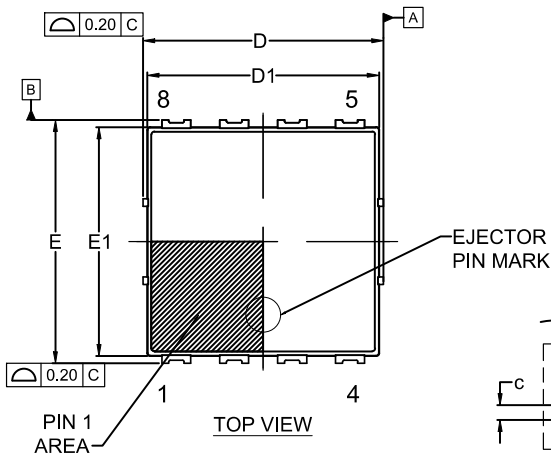


Figure 13. Thermal Characteristics

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PACKAGE DIMENSIONS

DFNW8 8.3x8.4, 2P
CASE 507AP
ISSUE A




NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	1.00	1.10	1.20
A1	0.00	--	0.05
b	0.90	1.00	1.10
b1	0.43	0.53	0.63
c	0.23	0.28	0.33
D	8.20	8.30	8.40
D1	7.90	8.00	8.10
D2	6.80	6.90	7.00
D3	6.90	7.00	7.10
E	8.30	8.40	8.50
E1	7.80	7.90	8.00
E2	5.24	5.34	5.44
E3	0.25	0.35	0.45
e	2.00 BSC		
e/2	1.00 BSC		
e1	2.70 BSC		
e1/2	1.35 BSC		
K	1.50	1.57	1.70
L	0.64	0.74	0.84
L1	0.67	0.77	0.87
Θ	0°	--	12°

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